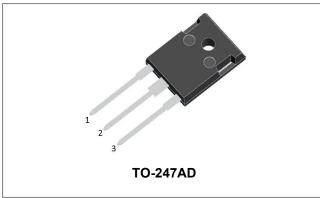


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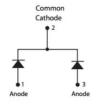




## MBR90200WT SCHOTTKY RECTIFIER



# Circuit Diagram



### **Features**

- 175 °C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

## Maximum Ratings(limiting values, at 25 °C unless otherwise specified):

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	200	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=155°C, rectangular wave form	45(Per Leg) 90(Per Device)	А
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	860	Α

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V <sub>F1</sub>	@ 45A, Pulse, T <sub>J</sub> = 25 °C	0.89	0.96	V
(Per Leg)*	V <sub>F2</sub>	@ 45A, Pulse, T <sub>J</sub> = 125 °C	0.78	0.86	V
Reverse Current (Per Leg)*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	0.0004	1	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125  ^{\circ}\text{C}$	0.10	25.0	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	740	900	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $<sup>^*\,</sup>$  Pulse width < 300  $\mu s,\,$  duty cycle < 2%

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •



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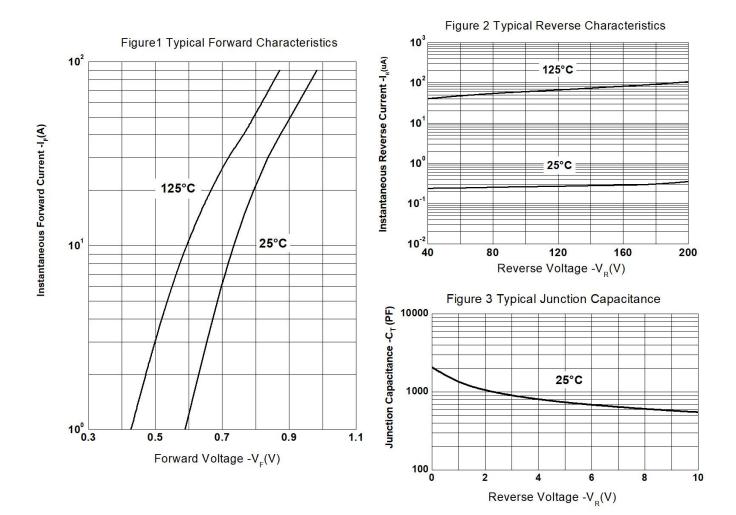




## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Case to Heat Sink	R <sub>θJCH</sub>	DC operation	0.25	°C/W
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	DC operation	0.47	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

## **Ratings and Characteristics Curves**



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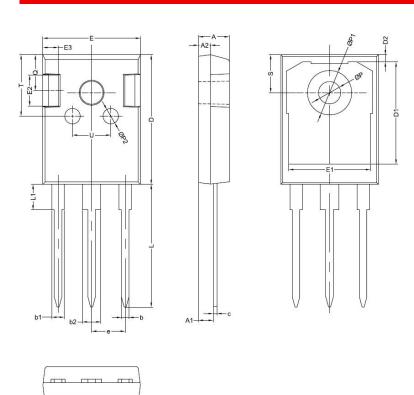


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### **Mechanical Dimensions TO-247AD**

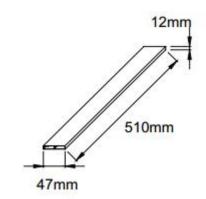


OVMDOL	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
Α	4.80	5.00	5.20	
A1	2.20	2.41	2.61	
A2	1.90	2.00	2.10	
b	1.10	1.20	1.40	
b1	1.80	2.00	2.20	
b2	2.80	3.00	3.20	
С	0.50	0.60	0.75	
D	20.30	21.00	21.20	
D1		16.55		
D2		1.20		
D2 E	15.45	15.80	16.00	
<u></u>		13.30		
E2		5.00		
E3		2.50		
е		5.44		
L	19.42	19.92	20.70	
L1		4.13		
Р	3.50	3.60	3.70	
P1	7.1		7.40	
P2		2.50		
		5.80		
Q S T	6.05	6.15	6.25	
T		10.00		
U		6.20		

## **Ordering Information:**

Device	Package	Shipping	
MBR90200WT	TO-247AD(Pb-Free)	25pcs / tube	

## **Tube Specification**



## **Marking Diagram**



Where XXXXX is YYWWL

MBR = Device Type 90 = Forward Current (90A) 200 = Reverse Voltage (200V) WT = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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#### **MBR90200WT**



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